

2SC2320

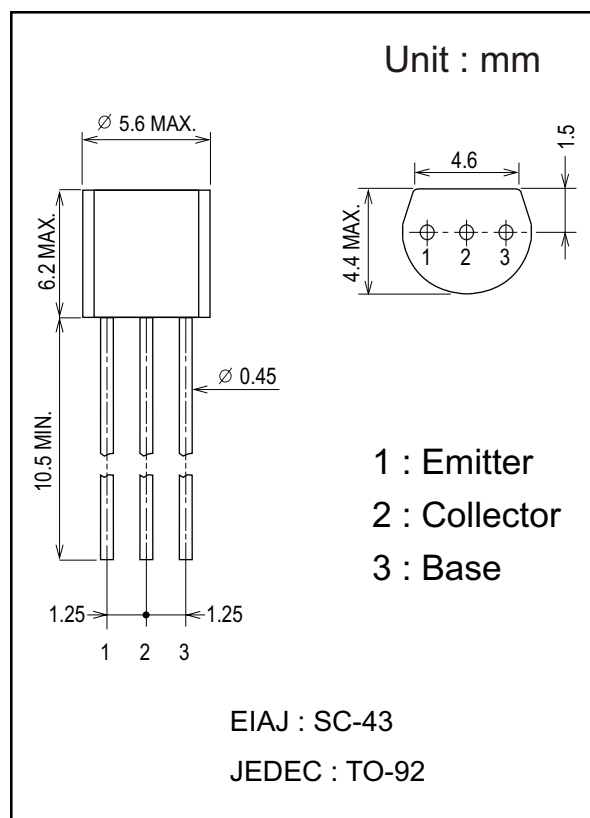
Audio Frequency Voltage Amplifier Applications
Low Noise Amplifier Applications

NPN Epitaxial Planar Silicon Transistor

Excellent hFE Linearity
Complementary to 2SA999

MAXIMUM RATINGS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	50	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector-Emitter Voltage	V _{CEO}	50	V
Collector Current	I _c	200	mA
Collector Power Dissipation	P _c	300	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~+125	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _c = 100μA, R _{BE} = ∞	50			V
Collector Cut-off current	I _{cBO}	V _{CB} = 50V, I _E = 0			0.1	μA
Emitter Cut-off current	I _{EBO}	V _{EB} = 6V, I _c = 0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} = 6V, I _c = 1mA	90		800	
DC Current Gain	h _{FE}	V _{CE} = 6V, I _c = 0,1mA	50			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 100mA, I _B = 10mA			0.3	V
Transition Frequency	f _T	V _{CE} = 6V, I _E = 10mA		200		MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 6V, I _E = 0, f = 1MHz		3,5		pF
Noise Figure	NF	V _{CE} = 6V, I _E = 0,3mA f = 100Hz, R _G = 10kΩ			2	dB

hFE Rank classification :

Rank	D	E	F	G
hFE	90~180	150~300	250~500	400~800

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